

Supplementary Information

Efficacious multifunction codoping strategy on the room-temperature solution-processed hole transport layer for realizing high-performance perovskite solar cells

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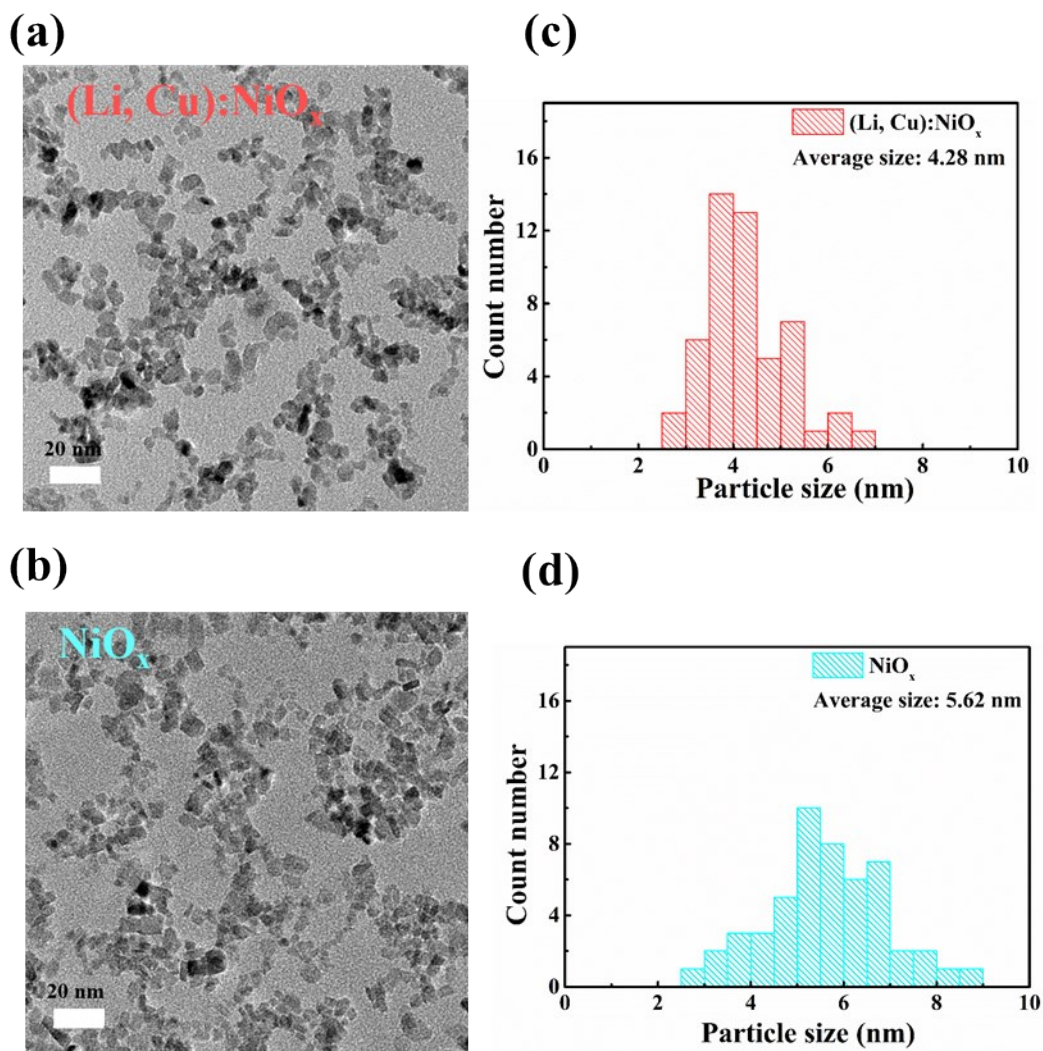


Fig. S1 TEM image of as-synthesized (a) (Li,Cu):NiO_x NPs and (b) pristine NiO_x and. Size distribution of (c) (Li, Cu):NiO_x and (d) pristine NiO_x NPs.

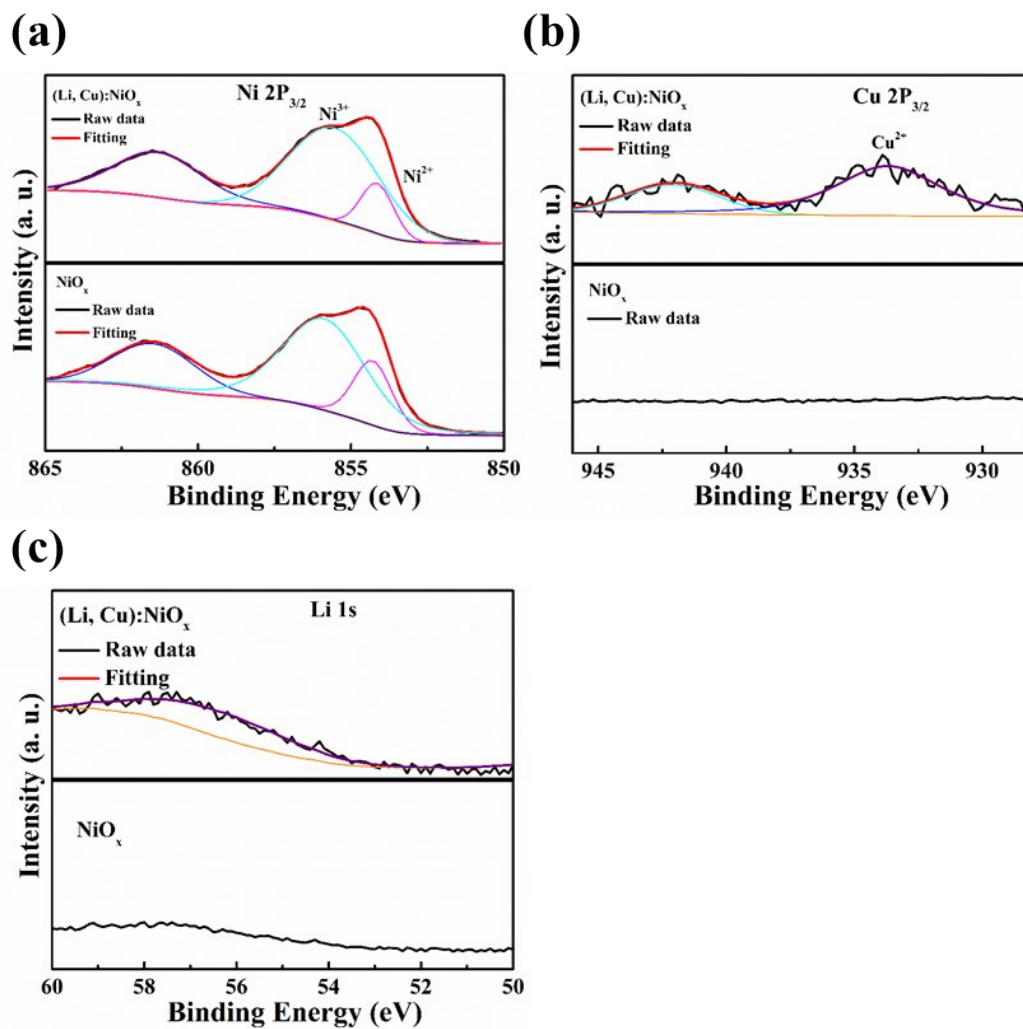


Fig. S2 High-resolution XPS spectra of (a) Ni 2p_{3/2}, (b) Cu 2p_{3/2} and (c) Li 1s elements for NiO_x and (Li,Cu):NiO_x NPs.

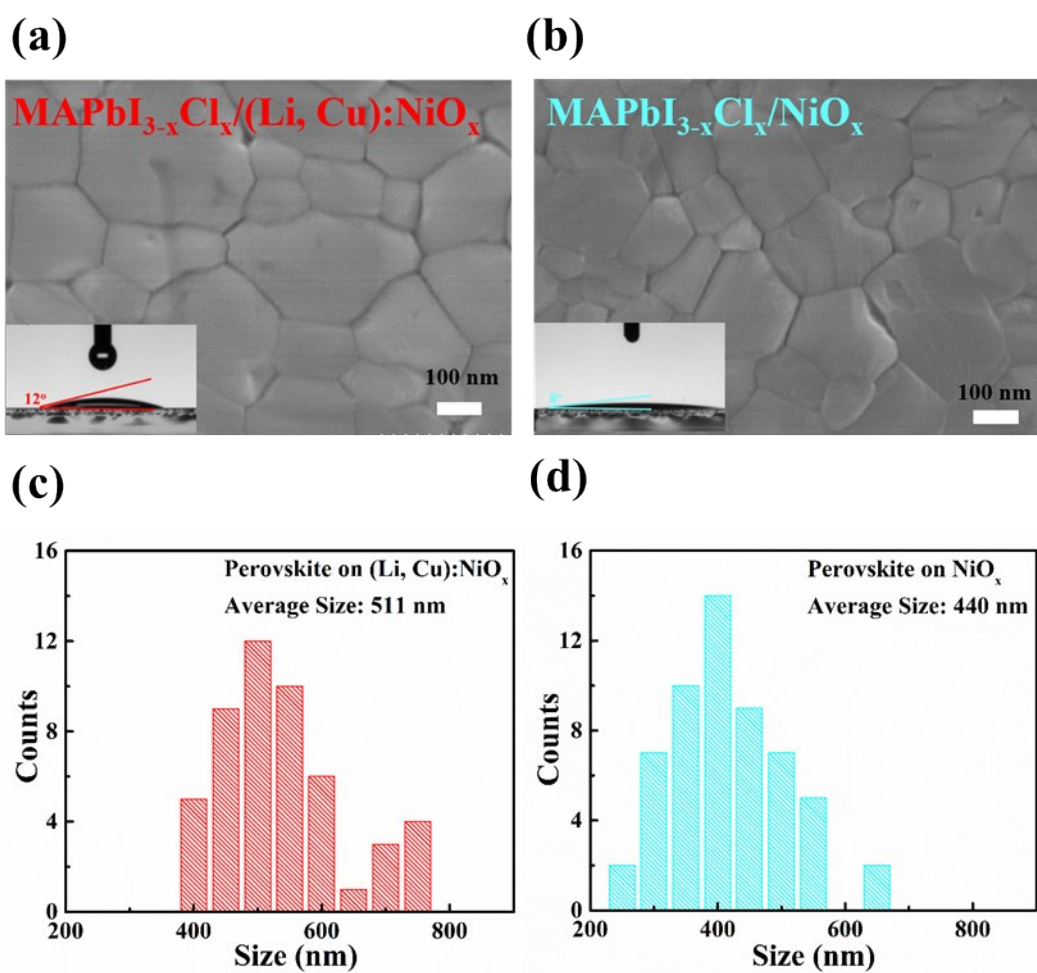


Fig. S3 SEM images of the perovskite film on (a) (Li,Cu):NiO_x, and (b) NiO_x films on ITO glass. Inserting is contact angle images of (Li,Cu):NiO_x, and NiO_x films, respectively. Size distribution of perovskite crystals on (c) (Li,Cu):NiO_x and (d) pristine NiO_x NPs, respectively.

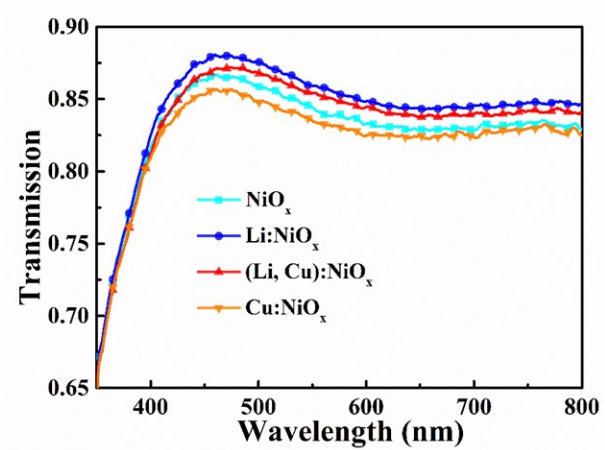


Fig. S4 Transmittance spectra of pristine NiO_x , Li:NiO_x , $(\text{Li,Cu}):NiO_x$, and Cu:NiO_x films on ITO glass.

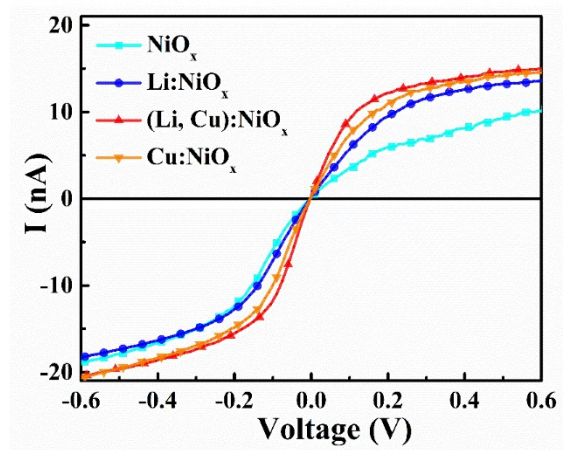


Fig. S5 I-V conducting curves of pristine NiO_x, Li:NiO_x, (Li,Cu):NiO_x, and Cu:NiO_x films measured from the c-AFM mode.

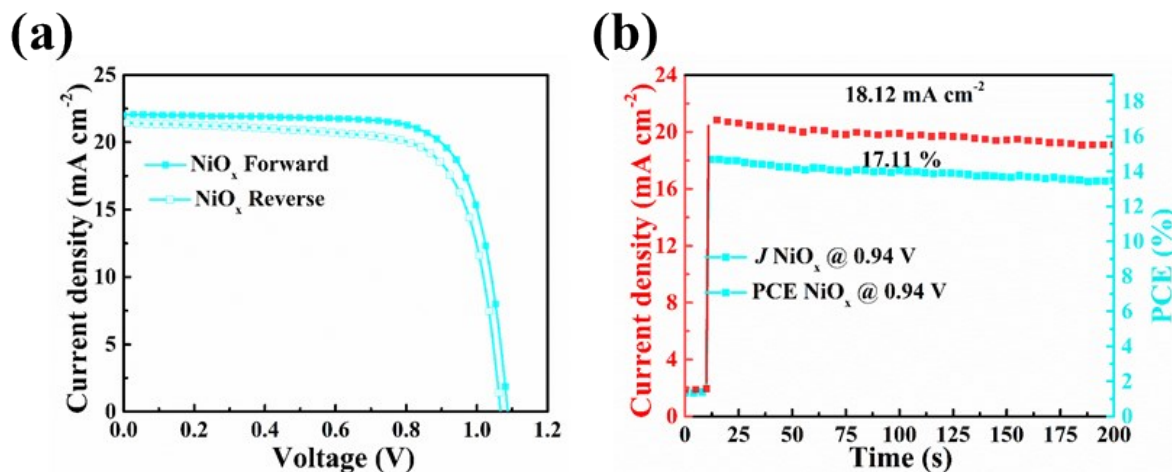


Fig. S6 (a) *J*-*V* characteristics of the best NiO_x based PSCs extracted from forward and reverse sweeping. (b) Steady photocurrent (red) and PCE (blue) under 1 Sun illumination of the best NiO_x based PSCs.

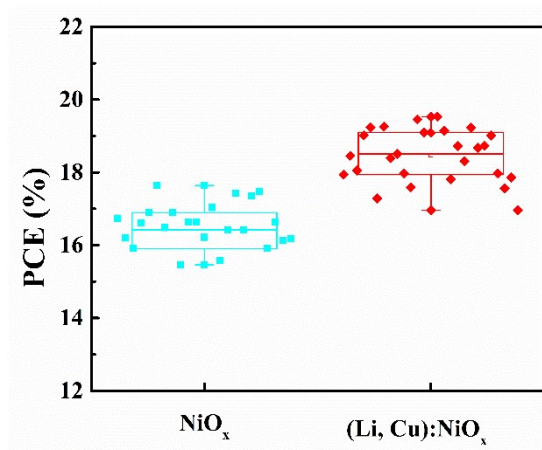


Fig. S7 PCE histogram of 30 pristine NiO_x and $(\text{Li, Cu}): \text{NiO}_x$ based PSC devices.

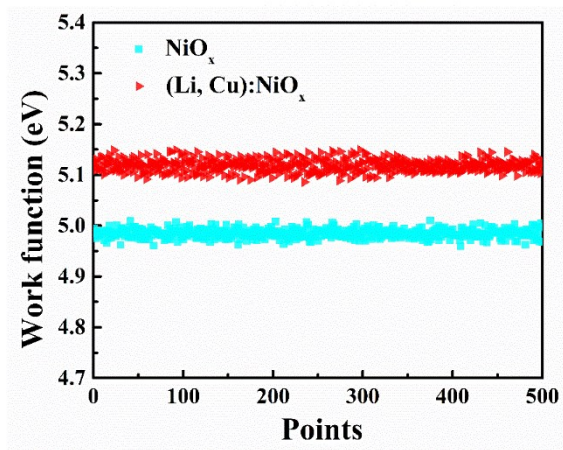


Fig. S8 Work function of $(\text{Li, Cu}): \text{NiO}_x$ HTL from Kelvin Probe.

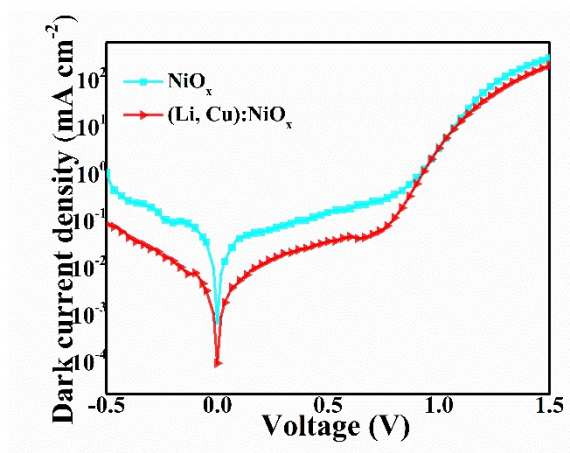


Fig. S9 The dark J - V curves of the best-inverted PSCs based on pristine NiO_x and (Li,Cu):NiO_x.

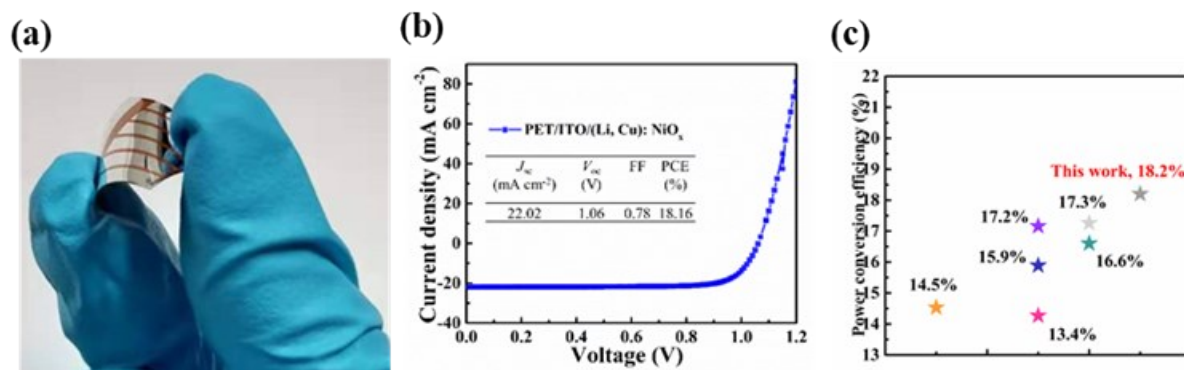


Fig. S10 (a) Photograph of a typical flexible PSC. (b) J-V characterization of (Li,Cu):NiO_x HTL based flexible device. (c) The efficiency of reported NiO_x based flexible devices.

Table S1 Performance of the reported planar PSCs based on NiO_x and doped NiO_x film.

Device Architecture	V _{oc} (V)	J _{sc} (mA cm ⁻²)	FF	PCE (%)	Method	Ref.
FTO/NiO _x /Cs _{0.05} (MA _{0.17} FA _{0.83}) _{0.95} Pb(I _{0.9} Br _{0.1}) ₃ /PCBM/TiO _x /Ag	1.10	23.0	0.81	20.65	NPs	1
ITO/NiO _x /MA _{1-y} FA _y PbI _{3-x} Cl _x /PCBM/BCP/Ag	1.12	23.7	0.76	20.2	Combustion	2
ITO/NiO _x /MAPbI ₃ /C ₆₀ /SnO ₂ /Ag	1.12	21.8	0.77	18.8	Sol-gel	3
ITO/NiO _x /Cs _{0.05} (MA _{0.17} FA _{0.83}) _{0.95} Pb(I _{0.9} Br _{0.1}) ₃ /PCBM/ZnO/Al	1.02	22.2	0.82	18.6	NPs	4
ITO/NiO _x /MAPbI ₃ /PCBM/Ti(Nb)O _x /Ag	1.07	21.9	0.79	18.5	NPs	5
FTO/NiO _x /MAPbI ₃ /PCBM/BCP/Ag	1.00	22.9	0.80	18.2	Sol-gel	6
ITO/NiO _x /MAPbI ₃ /C ₆₀ /Bis-C ₆₀ /Ag	1.03	21.8	0.78	17.7	NPs	7
ITO/NiO _x /MAPbI ₃ /PCBM/Bis-C ₆₀ /Ag	1.10	21.7	0.75	17.6	Sol-gel	8
ITO/NiO _x /MAPbI ₃ /PCBM/BCP/Ag	1.02	21.8	0.79	17.6	Spray pyrolysis	9
ITO/PLD-NiO _x /MAPbI ₃ /PCBM/LiF/Ag	1.06	20.2	0.81	17.3	PLD	10
ITO/NiO _x /MAPbI ₃ /PCBM/Ag	1.04	22.5	0.72	16.9	Electrodeposited	11
ITO/NiO _x /MAPbI ₃ /PCBM/Ag	1.07	20.6	0.75	16.5	NPs	12
ITO/NiO _x /MAPbI ₃ /PCBM/Ag	1.04	21.9	0.72	16.4	ALD	13
ITO/NiO _x /MAPbI ₃ /PCBM/BCP/Ag	0.98	19.7	0.64	12.4	Sputtering	14
ITO/Cu:NiO _x /MAPbI ₃ /PCBM/C ₆₀ /Ag	1.12	22.2	0.81	20.1	NPs	15
ITO/Zn:NiO _x /MAPbI ₃ /PCBM/C ₆₀ /Ag	1.10	22.8	0.78	19.6	Sol-gel	16
FTO/Sr:NiO _x /MAPbI ₃ /PCBM/BCP/Ag	1.14	22.7	0.76	19.5	Sol-gel	17
FTO/Cs:NiO _x /MAPbI ₃ /PCBM/Zracac/Ag	1.12	21.8	0.79	19.4	Sol-gel	18
FTO/Ca:NiO _x /MAPbI ₃ /PCBM/BCP/Ag	1.13	22.3	0.74	18.7	Sol-gel	17
FTO/Mg:NiO _x /MAPbI ₃ /PCBM/BCP/Ag	1.10	22.4	0.75	18.3	Sol-gel	17
ITO/K:NiO _x /MAPbI ₃ /PCBM:C ₆₀ /BCP/Ag	1.01	22.8	0.78	18.1	Sol-gel	19
FTO/Li:NiO _x /MAPbI ₃ /PCBM/Al	1.03	19.4	0.72	14.2	Sol-gel	20
ITO/Cu:NiO _x /MAPbI ₃ /C ₆₀ /Bis-C ₆₀ /Ag	1.05	22.2	0.76	17.7	Combustion	21
ITO/Ag:NiO _x /MAPbI ₃ /PCBM/C ₆₀ /Ag	1.09	21.1	0.78	17.3	Sol-gel	22
ITO/Cs:NiO _x /MAPbI ₃ /PCBM/C ₆₀ /Au	1.03	21.4	0.78	17.2	Sol-gel	23
ITO/Rb:NiO _x /MAPbI ₃ /PCBM/BCP/Ag	1.05	21.8	0.75	17.2	Sol-gel	24
ITO/Cu:NiO _x /MAPbI ₃ /C ₆₀ /Bis-C ₆₀ /Ag	1.11	19.1	0.72	15.4	Sol-gel	25
FTO/La:NiO _x /MAPbI ₃ /PCBM/BCP/Ag	1.03	20.7	0.71	15.3	Sol-gel	26
ITO/Co:NiO _x /MAPbI ₃ /PCBM/BCP/Ag	1.06	17.3	0.79	14.5	NPs	27
ITO/Li,Ag:NiO _x /MAPbI ₃ /PCBM/BCP/Ag	1.13	21.3	0.80	19.2	Sol-gel, 300 °C	28
FTO/Li _{0.05} Mg _{0.15} Ni _{0.8} O _x /Psk/Ti(Nb)O _x /Ag	1.12	22.7	0.77	19.6	Spray pyrolysis, 500 °C	29
ITO/Li,Pb:NiO _x /MAPbI ₃ /PCBM/BCP/Ag	1.01	21.3	0.79	17.4	Sol-gel, 450 °C	30
ITO/Li,Cu:NiO _x /MAPbI ₃ /PCBM/Ag	0.96	20.8	0.72	14.5	Sol-gel, 500 °C	31
ITO/(Li,Cu):NiO_x/MAPbI_{3-x}Cl_x/PCBM:C₆₀/Zracac/Ag	1.11	23.1	0.81	20.8	NPs, 25 °C	this work

Table S2 The WF variation of pristine NiO_x and doped NiO_x film characterized by Kelvin-Probe measurements. ΔE_F is defined as the energy level offsets of the doped film and pristine film.

Material	WF (eV)	ΔE_F (eV)
NiO _x	4.99±0.01	0
Li:NiO _x	5.07±0.0	0.08
(Li, Cu):NiO _x	5.12±0.0	0.13
Cu:NiO _x	5.02±0.0	0.03

Table S3 Summary of device performance with (Li,Cu):NiO_x HTL treated at varying temperatures. The best PCEs are shown in brackets.

Samples	V _{oc} (V)	J _{sc} (mA cm ⁻²)	FF	PCE (%)
RT	1.08	22.61	0.78	19.01(20.83)
100 °C	1.05	21.88	0.80	18.36(18.63)
150 °C	1.04	21.96	0.80	18.30(18.52)
200 °C	1.04	21.95	0.81	18.49(18.67)
250 °C	1.04	22.12	0.81	18.64(19.00)
300 °C	1.02	21.99	0.81	17.99(18.60)

Table S4 Devices performance based on NiO_x HTL with different doping elements.

Doping element	Scan direction	J_{sc} (mA cm ⁻²)	V_{oc} (V)	FF	PCE (%)
N/A	Forward	22.02	1.09	0.75	17.91
	Reverse	21.45	1.07	0.73	16.75
Li	Forward	22.69	1.08	0.71	17.49
	Reverse	22.46	1.07	0.71	17.10
(Li, Cu)	Forward	23.07	1.09	0.80	20.08
	Reverse	22.84	1.10	0.80	20.07
Cu	Forward	22.54	1.05	0.75	17.76
	Reverse	21.67	1.03	0.66	14.89

Table S5 Devices performance based on (Li,Cu):NiO_x HTL with different doping concentrations.

Total doping concentration (%)	Ratio of Li/Cu	Scan direction	J_{sc} (mA cm ⁻²)	V_{oc} (V)	FF	PCE (%)
0	0	Forward	22.02	1.09	0.75	17.91
		Reverse	21.45	1.07	0.73	16.75
5	2/1	Forward	23.07	1.09	0.80	20.08
		Reverse	22.84	1.10	0.80	20.07
10	2/1	Forward	22.23	1.05	0.74	17.37
		Reverse	21.84	1.03	0.71	16.14
20	2/1	Forward	16.55	1.01	0.72	12.00
		Reverse	15.58	0.99	0.60	9.19

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